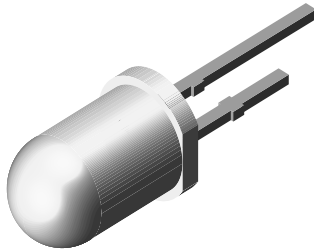


Infrared Emitting Diode, 950 nm, GaAs



94 8390

DESCRIPTION

TSUS5200 is an infrared, 950 nm emitting diode in GaAs technology molded in a blue-gray tinted plastic package.

FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm): \varnothing 5
- Leads with stand-off
- Peak wavelength: $\lambda_p = 950$ nm
- High reliability
- Angle of half intensity: $\varphi = \pm 15^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Infrared remote control and free air transmission systems with low forward voltage and small package requirements
- Emitter in transmissive sensors
- Emitter in reflective sensors

PRODUCT SUMMARY

| COMPONENT | I_e (mW/sr) | φ (deg) | λ_p (nm) | t_r (ns) |
|-----------|---------------|-----------------|------------------|------------|
| TSUS5200 | 20 | ± 15 | 950 | 800 |
| TSUS5201 | 25 | ± 15 | 950 | 800 |
| TSUS5202 | 30 | ± 15 | 950 | 800 |

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

| ORDERING CODE | PACKAGING | REMARKS | PACKAGE FORM |
|---------------|-----------|------------------------------|-------------------|
| TSUS5200 | Bulk | MOQ: 4000 pcs, 4000 pcs/bulk | T-1 $\frac{3}{4}$ |
| TSUS5201 | Bulk | MOQ: 4000 pcs, 4000 pcs/bulk | T-1 $\frac{3}{4}$ |
| TSUS5202 | Bulk | MOQ: 4000 pcs, 4000 pcs/bulk | T-1 $\frac{3}{4}$ |

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT |
|-------------------------------------|--|------------|---------------|------------|
| Reverse voltage | | V_R | 5 | V |
| Forward current | | I_F | 150 | mA |
| Peak forward current | $t_p/T = 0.5, t_p = 100 \mu s$ | I_{FM} | 300 | mA |
| Surge forward current | $t_p = 100 \mu s$ | I_{FSM} | 2.5 | A |
| Power dissipation | | P_V | 170 | mW |
| Junction temperature | | T_j | 100 | $^\circ C$ |
| Operating temperature range | | T_{amb} | - 40 to + 85 | $^\circ C$ |
| Storage temperature range | | T_{stg} | - 40 to + 100 | $^\circ C$ |
| Soldering temperature | $t \leq 5$ s, 2 mm from case | T_{sd} | 260 | $^\circ C$ |
| Thermal resistance junction/ambient | J-STD-051, leads 7 mm, soldered on PCB | R_{thJA} | 230 | K/W |

Note

$T_{amb} = 25 \text{ }^\circ C$, unless otherwise specified

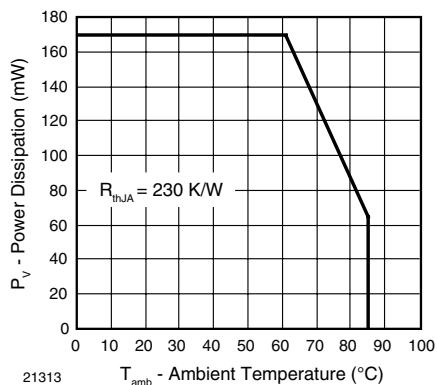


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

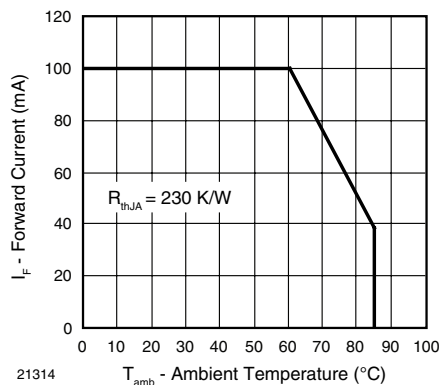


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS | | | | | | |
|---|---|-----------------------------|------|-------|------|------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| Forward voltage | I _F = 100 mA, t _p = 20 ms | V _F | | 1.3 | 1.7 | V |
| Temperature coefficient of V _F | I _F = 100 mA | TK _{V_F} | | - 1.3 | | mV/K |
| Reverse current | V _R = 5 V | I _R | | | 100 | μA |
| Junction capacitance | V _R = 0 V, f = 1 MHz, E = 0 | C _j | | 30 | | pF |
| Temperature coefficient of φ _e | I _F = 20 mA | TKφ _e | | - 0.8 | | %/K |
| Angle of half intensity | | φ | | ± 15 | | deg |
| Peak wavelength | I _F = 100 mA | λ _p | | 950 | | nm |
| Spectral bandwidth | I _F = 100 mA | Δλ | | 50 | | nm |
| Temperature coefficient of λ _p | I _F = 100 mA | TKλ _p | | 0.2 | | nm/K |
| Rise time | I _F = 100 mA | t _r | | 800 | | ns |
| | I _F = 1.5 A | t _r | | 400 | | ns |
| Fall time | I _F = 100 mA | t _f | | 800 | | ns |
| | I _F = 1.5 A | t _f | | 400 | | ns |
| Virtual source diameter | | d | | 3.8 | | mm |

Note

T_{amb} = 25 °C, unless otherwise specified



TSUS5200, TSUS5201, TSUS5202

Infrared Emitting Diode, 950 nm, GaAs Vishay Semiconductors

| TYPE DEDICATED CHARACTERISTICS | | | | | | | |
|--------------------------------|---|----------|----------|------|------|------|-------|
| PARAMETER | TEST CONDITION | PART | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| Forward voltage | $I_F = 1.5 \text{ A}$, $t_p = 100 \mu\text{s}$ | TSUS5200 | V_F | | 2.2 | 3.4 | V |
| | | TSUS5201 | V_F | | 2.2 | 3.4 | V |
| | | TSUS5202 | V_F | | 2.2 | 2.7 | V |
| Radiant intensity | $I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$ | TSUS5200 | I_e | 10 | 20 | 50 | mW/sr |
| | | TSUS5201 | I_e | 15 | 25 | 50 | mW/sr |
| | | TSUS5202 | I_e | 20 | 30 | 50 | mW/sr |
| | $I_F = 1.5 \text{ A}$, $t_p = 100 \mu\text{s}$ | TSUS5200 | I_e | 95 | 180 | | mW/sr |
| | | TSUS5201 | I_e | 120 | 230 | | mW/sr |
| | | TSUS5202 | I_e | 170 | 280 | | mW/sr |
| Radiant power | $I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$ | TSUS5200 | ϕ_e | | 13 | | mW |
| | | TSUS5201 | ϕ_e | | 14 | | mW |
| | | TSUS5202 | ϕ_e | | 15 | | mW |

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

BASIC CHARACTERISTICS

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

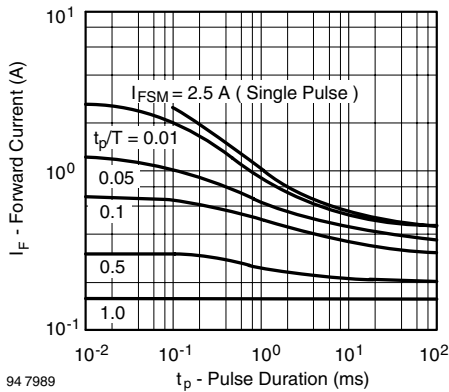


Fig. 3 - Pulse Forward Current vs. Pulse Duration

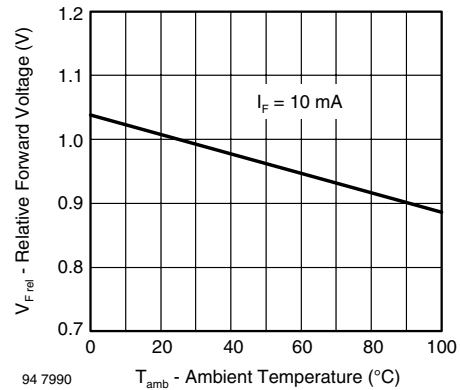


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

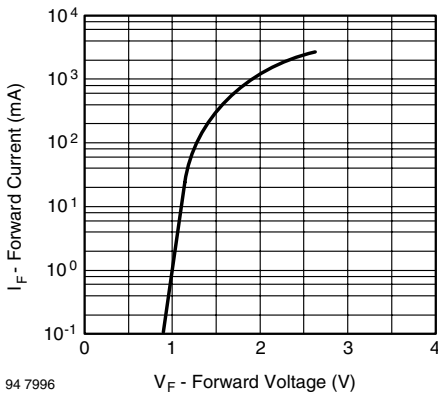


Fig. 4 - Forward Current vs. Forward Voltage

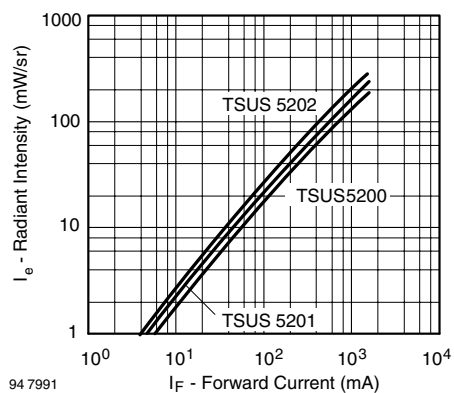


Fig. 6 - Radiant Intensity vs. Forward Current

TSUS5200, TSUS5201, TSUS5202



Vishay Semiconductors Infrared Emitting Diode, 950 nm, GaAs

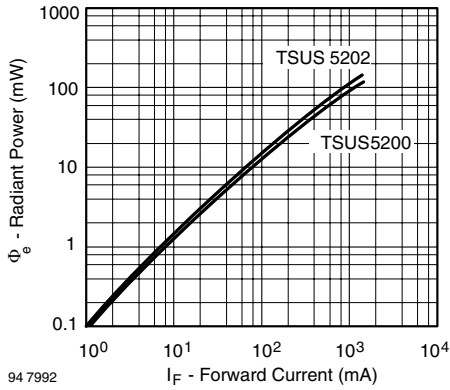


Fig. 7 - Radiant Power vs. Forward Current

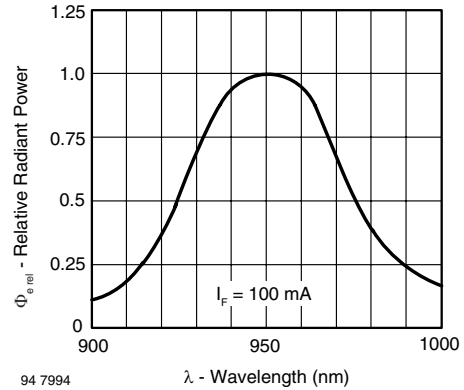


Fig. 9 - Relative Radiant Power vs. Wavelength

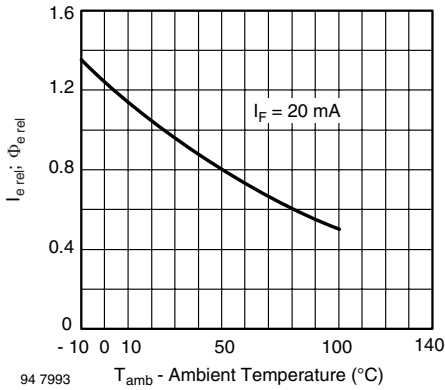


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

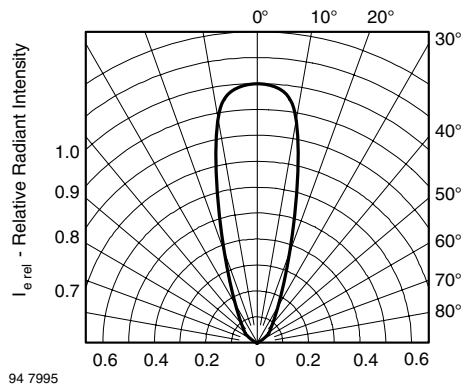
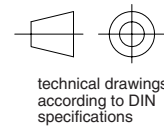
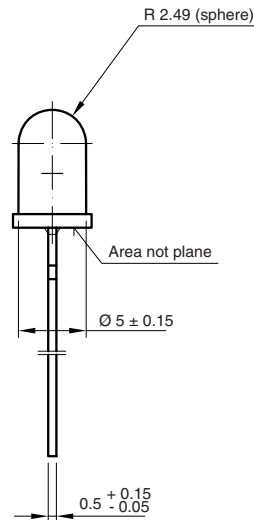
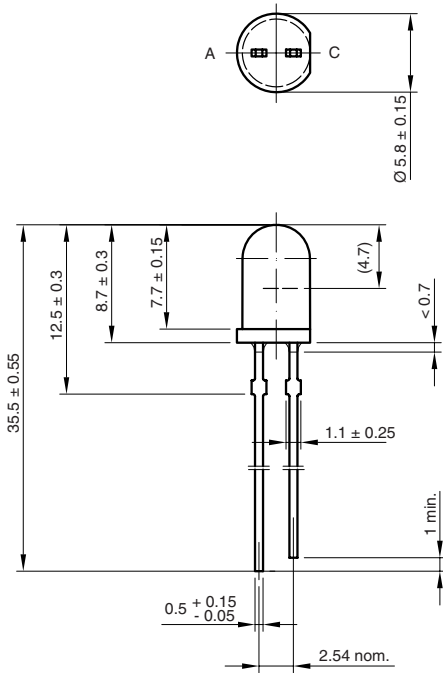


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



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